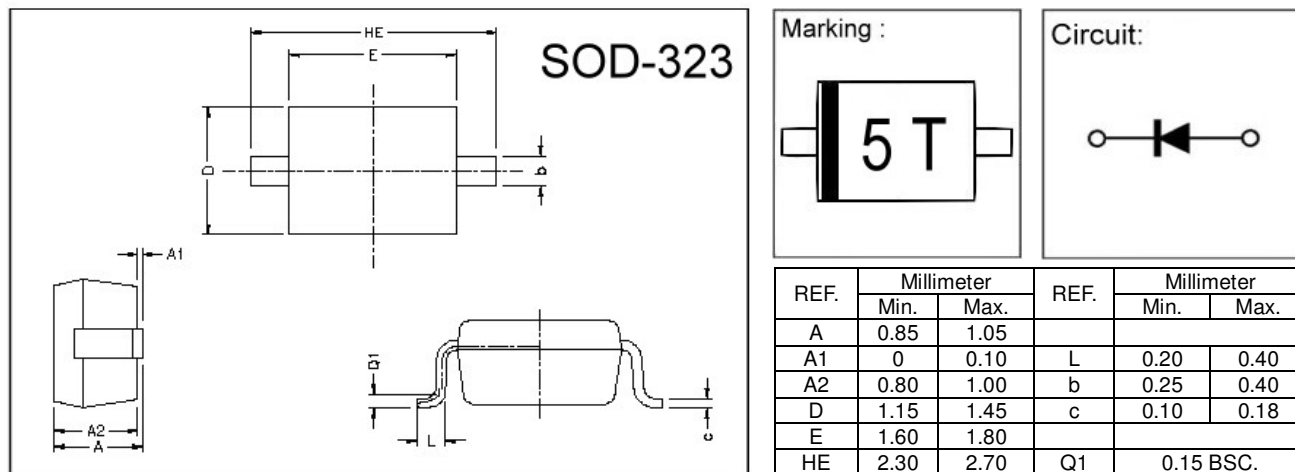


GD411SD**SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.5A****Description**

The GD411SD is designed for low power rectification.

Package Dimensions**Absolute Maximum Ratings at TA = 25°C**

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	V
Maximum RMS Voltage	V _{RMS}	28	V
Maximum DC Blocking Voltage	V _{DC}	20	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	20	pF
Maximum Average Forward Rectified Current	I _o	0.5	A
Total Power Dissipation	PD	225	mW

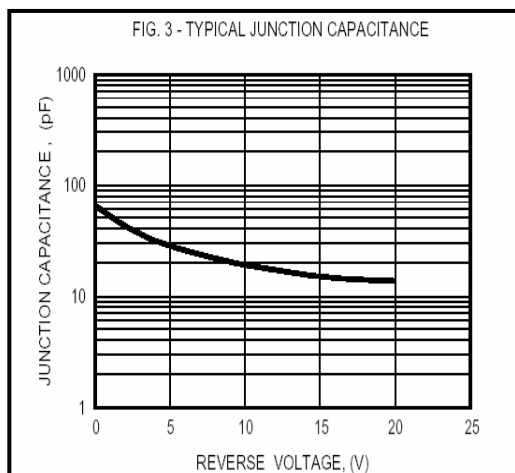
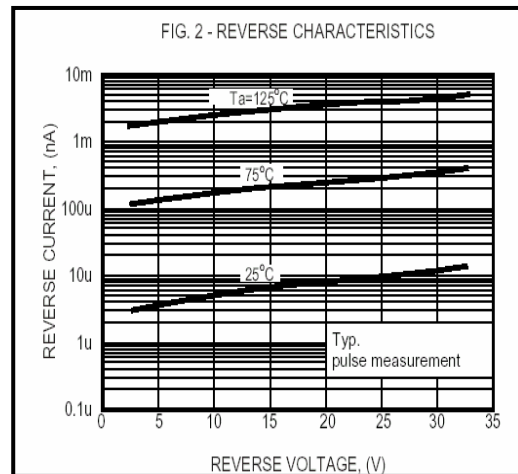
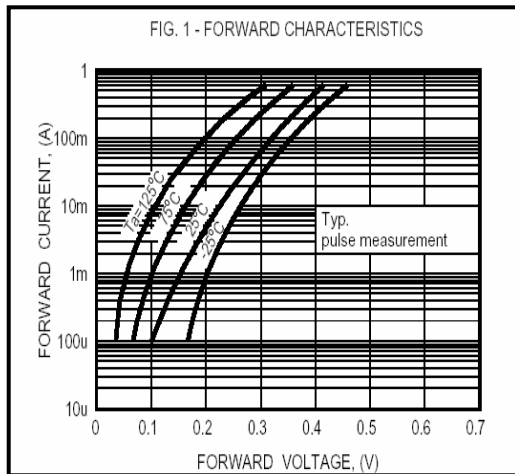
Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	40	-	-	V	IR=100μA
Maximum Instantaneous Forward Voltage	V _F	-	-	300	mV	IF1=10mA
		-	-	500		IF2=500mA
Maximum Average Reverse Current	I _R	-	-	30	uA	VR=10V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.

2. ESD sensitive product handling required.

Characteristics Curve

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